

GL195

PNP SILICON PLANAR MEDIUM POWER TRANSISTOR

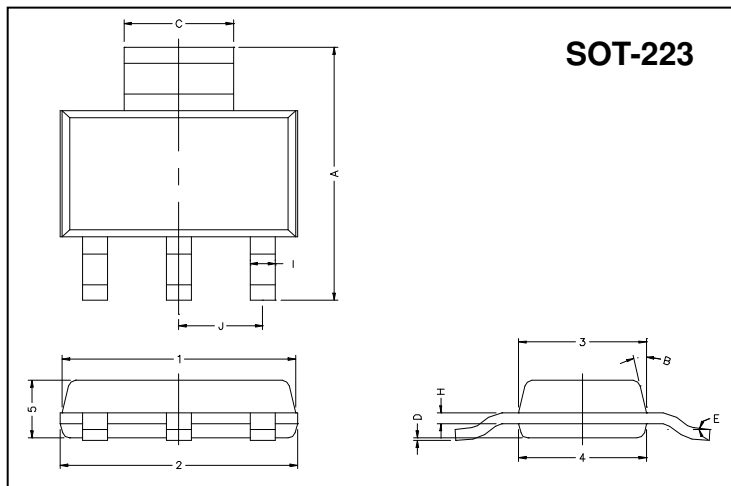
Description

The GL195 is designed for medium power amplifier applications.

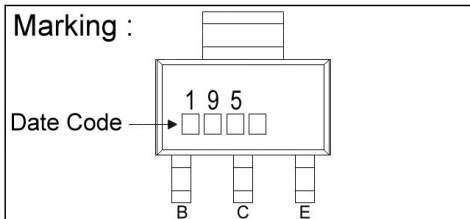
Features

- -60 Volt V_{CE0}
- 1 Amp continuous current
- Complementary to GL194

Package Dimensions



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.70	7.30	B	13°TYP.	
C	2.90	3.10	J	2.30 REF.	
D	0.02	0.10	1	6.30	6.70
E	0°	10°	2	6.30	6.70
I	0.60	0.80	3	3.30	3.70
H	0.25	0.35	4	3.30	3.70
			5	1.40	1.80

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

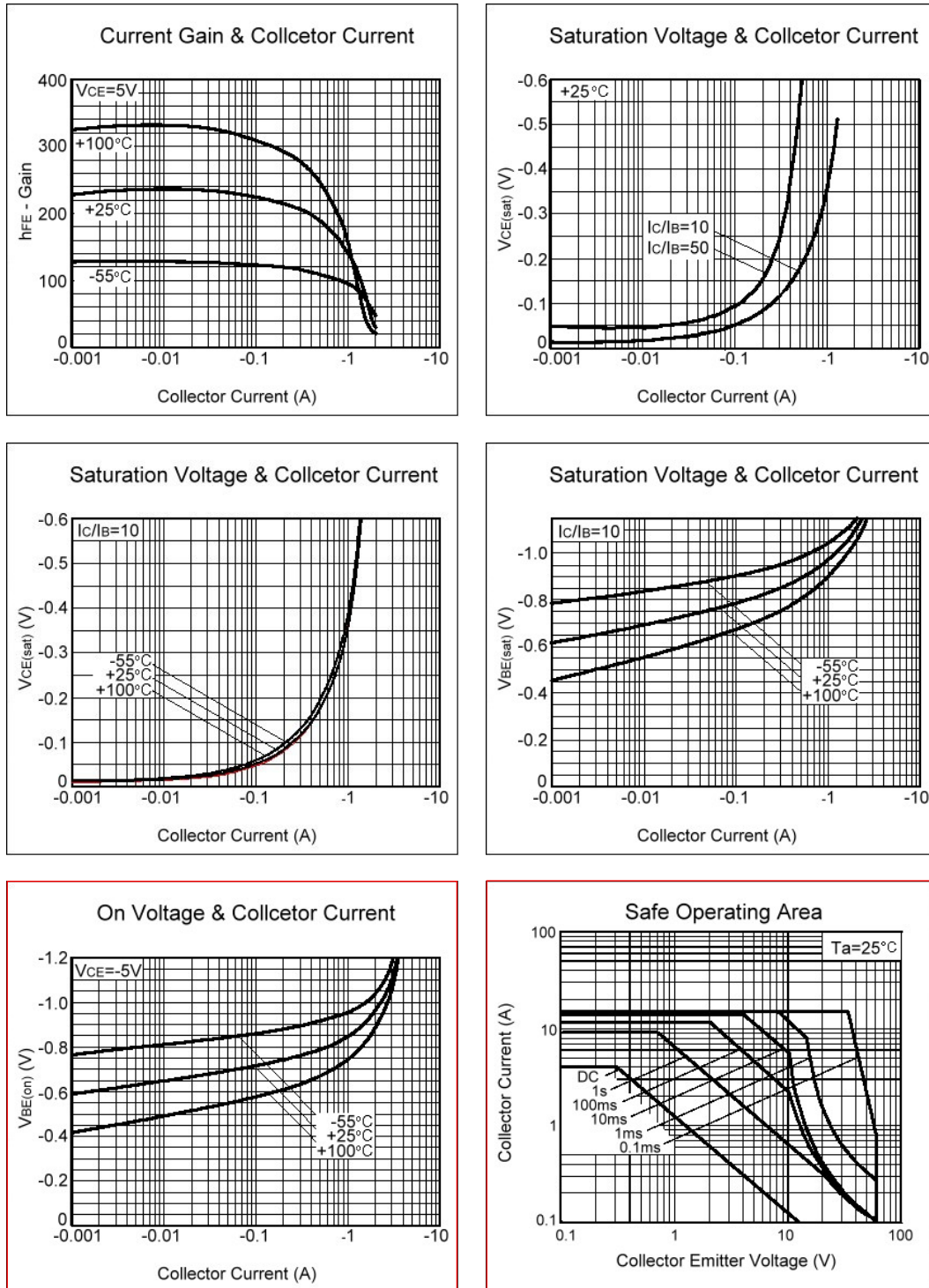
Parameter	Symbol	Ratings	Unit
Junction Temperature	T_j	+150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~+150	$^\circ\text{C}$
Collector to Base Voltage	V_{CB0}	-80	V
Collector to Emitter Voltage	V_{CE0}	-60	V
Emitter to Base Voltage	V_{EB0}	-5	V
Collector Current (DC)	I_c	-1	A
Collector Current (Pulse)	I_c	-2	A
Base Current	I_B	-200	mA
Total Power Dissipation	P_D	2	W

Electrical Characteristics ($T_a = 25^\circ\text{C}$, unless otherwise stated)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
V_{CB0}	-80	-	-	V	$I_c = -100\mu\text{A}$, $I_E = 0$
$*V_{CE0}$	-60	-	-	V	$I_c = -10\text{mA}$, $I_B = 0$
V_{EB0}	-5	-	-	V	$I_E = -100\mu\text{A}$, $I_c = 0$
I_{CB0}	-	-	-100	nA	$V_{CB} = -60\text{V}$, $I_E = 0$
I_{CES}	-	-	-100	nA	$V_{CES} = -60\text{V}$
I_{EBO}	-	-	-100	nA	$V_{EB} = -4\text{V}$, $I_c = 0$
$*V_{CE(sat)1}$	-	-	-0.3	V	$I_c = -500\text{mA}$, $I_B = -50\text{mA}$
$*V_{CE(sat)2}$	-	-	-0.6	V	$I_c = -1\text{A}$, $I_B = -100\text{mA}$
$*V_{BE(sat)}$	-	-	-1.2	V	$I_c = -1\text{A}$, $I_B = -100\text{mA}$
$*V_{BE(on)}$	-	-	-1.0	V	$V_{CE} = -5\text{V}$, $I_c = -1\text{A}$
$*h_{FE1}$	100	-	-		$V_{CE} = -5\text{V}$, $I_c = -1\text{mA}$
$*h_{FE2}$	100	-	300		$V_{CE} = -5\text{V}$, $I_c = -500\text{mA}$
$*h_{FE3}$	80	-	-		$V_{CE} = -5\text{V}$, $I_c = -1\text{A}$
$*h_{FE4}$	15	-	-		$V_{CE} = -5\text{V}$, $I_c = -2\text{A}$
f_T	150	-	-	MHz	$V_{CE} = -10\text{V}$, $I_c = -50\text{mA}$, $f = 100\text{MHz}$
C_{ob}	-	-	10	pF	$V_{CB} = -10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$

*Measured under pulse condition. Pulse width=300 μs , Duty Cycle $\leq 2\%$

Characteristics Curve



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